

## SOT-23 Plastic-Encapsulate Transistors

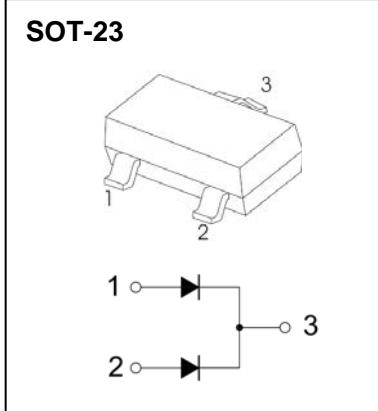
### **RB495D SCHOTTKY BARRIER DIODE**

#### **FEATURES**

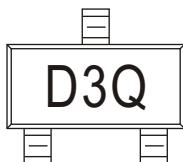
- Small Surface Mounting Type
- Low Forward Voltage
- Low Reverse Current
- High Reliability

#### **APPLICATIONS**

- General Rectification



#### **MARKING: D3Q**



D3Q = Device code

#### **MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted )**

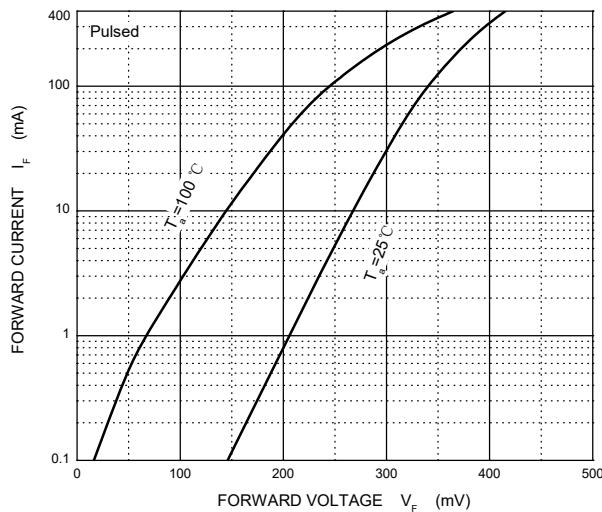
Symbol	Parameter	Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	40	V
$V_{RVM}$	Working Peak Reverse Voltage		
$V_{R(\text{RMS})}$	RMS Reverse Voltage	28	V
$I_o$	Continuous Forward Current	400	mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current@ $t=8.3\text{ms}$	2	A
$P_D$	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	400	$^\circ\text{C}/\text{W}$
$T_J$	Operating Junction Temperature Range	-40 ~ +125	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 ~ +150	$^\circ\text{C}$

#### **ELECTRICAL CHARACTERISTICS( $T_a=25^\circ\text{C}$ unless otherwise specified)**

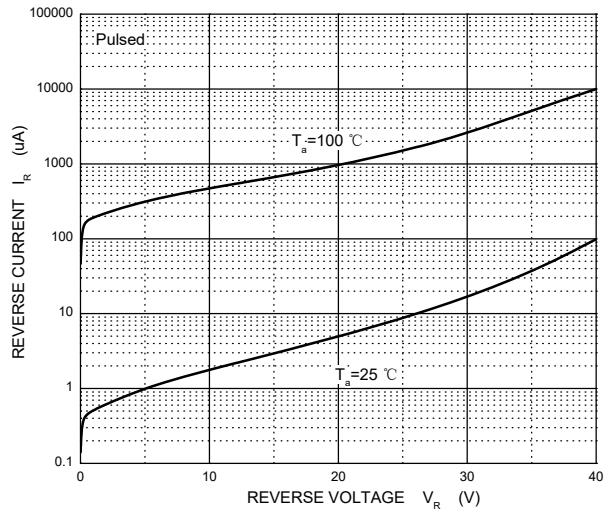
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(\text{BR})}$	$I_R=100\mu\text{A}$	25			V
Reverse current	$I_R$	$V_R=25\text{V}$			70	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=10\text{mA}$			0.3	V
		$I_F=200\text{mA}$			0.5	

### Typical Characteristics

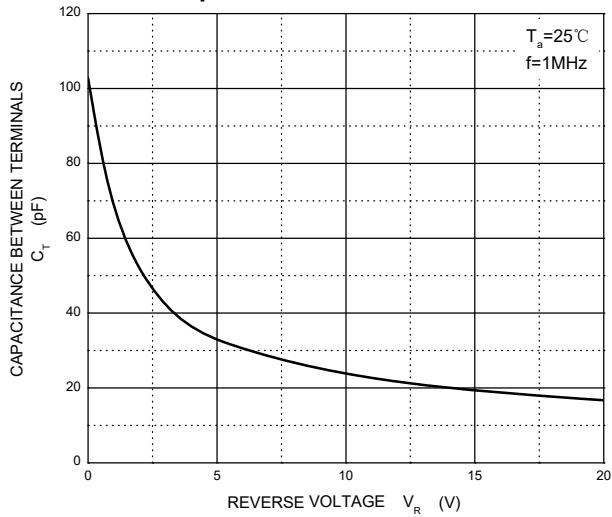
#### Forward Characteristics



#### Reverse Characteristics



#### Capacitance Characteristics



#### Power Derating Curve

